

Please replace paragraph number 0008 with the following amended paragraph:

A copper anti-diffusion conductive film 15 is formed along the surface of the anti-polishing layer 13 including the damascene pattern 14. A copper layer is formed enough to sufficiently bury the damascene pattern 14. A CMP process is then performed until the anti-polishing layer 13 is exposed, thus forming a copper wiring 16 within the damascene pattern 14. Thereafter, a copper anti-diffusion insulating film 100 and a second interlayer insulating film 17 are formed on the entire structure including the copper wiring 16.

Please replace paragraph number 0009 with the following amended paragraph:

In the above-mentioned method, in order to prevent diffusion of copper elements from the copper wiring 16, ~~to the outside~~, the copper wiring 16 is sealed using the copper anti-diffusion conductive film 15 and the copper anti-diffusion insulating film 100. In ~~the a~~ device having the copper wiring 16 formed by a conventional method, however, most of defective wirings are generated due to electro-migration and stress migration that take takes place at the interface between the copper anti-diffusion insulating film 100 and the copper anti-diffusion conductive film 15, as indicated by an arrow "A". This condition is caused by a lack in the bondability between the copper anti-diffusion insulating film 100 and the underlying layers 13, 15 and 16.

Please replace the title beginning on page ³ 4, line ¹⁹ 1 with the following:

SUMMARY OF THE INVENTION DISCLOSURE

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Please replace paragraph number 0010 with the following amended paragraph:

~~The present invention is directed to provide a~~ A method of forming a copper wiring ~~in a semiconductor device~~ within a damascene pattern is disclosed which is capable of enhancing the electrical properties ~~of the device~~, preventing an electrical short ~~condition~~ between neighboring copper wirings and facilitating subsequent processes through surface polishing, by ~~prohibiting~~ preventing electro-migration and by preventing stress migration of copper in the copper wiring ~~formed within a damascene pattern~~.

Please replace paragraph number 0014 with the following amended paragraph:

In the above method, the third step includes the steps of overly performing a chemical mechanical polishing process so that the top surface of the copper wiring is concaved and formed lower than the surface of the interlayer insulating film, and performing an annealing process so that the top surface of the copper wiring is changed from the concave shape to a convex shape while stabilizing the copper wiring.

Please replace paragraph number 0017 with the following amended paragraph:

Figs. 2A to 2C are sectional views for explaining a method of forming a copper wiring in a semiconductor device according to an one embodiment of the ~~present invention~~;

Please replace paragraph number 0018 with the following amended paragraph:

Figs. 3A to 3C are sectional views for explaining a method of forming a copper wiring in a semiconductor device according to another embodiment of the ~~present invention~~.

Please replace the title beginning on page 6, line ⁵14 as follows:

DETAILED DESCRIPTION OF THE

~~PRESENTLY~~ PREFERRED EMBODIMENTS

Please replace paragraph number 0019 with the following amended paragraph:

Now the preferred embodiments ~~according to the present invention~~ will be described with reference to the accompanying drawings. Since preferred embodiments are provided for the purpose ~~that the ordinary~~ of understanding for those skilled in the art, ~~are able to understand the present invention~~, they may be modified in various manners and the scope of ~~the present invention~~ this disclosure is not limited by the preferred embodiments described ~~later~~ herein.

Please replace paragraph number 0020 with the following amended paragraph:

Figs. 2A to 2C are sectional views for explaining a disclosed method of forming a copper wiring in a semiconductor device ~~according to an embodiment of the present invention~~.

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